Electronic Pr	Semester	3		
Course Code	BEC303	CIE Marks	50	
Teaching Hours/Week (L:T:P: S)	3:0:2	SEE Marks	50	
Total Hours of Pedagogy	40 hours Theory + 8-10 Lab slots	Total Marks	100	
Credits	04	Exam Hours		
Examination nature (SEE)	Theory/Practical/Viva-Voce /Term-work/Others			

Course objectives:

This course will enable students to

- Design and analyse the BJT circuits as an amplifier and voltage regulation.
- Design of MOSFET Amplifiers and analyse the basic amplifier configurations using small signal equivalent circuit models
- Design of operational amplifiers circuits as Comparators, DAC and filters.
- Understand the concept of positive and negative feedback.
- Analyze Power amplifier circuits in different modes of operation.
- Construct Feedback and Oscillator circuits using FET.
- Understand the thyristor operation and the different types of thyristors.

Teaching-Learning Process (General Instructions)

These are sample Strategies, which teacher can use to accelerate the attainment of the various course outcomes.

- 1. Lecture method (L) does not mean only traditional lecture method, but different type of teaching methods may be adopted to develop the outcomes.
- 2. Show Video/animation films to explain evolution of communication technologies.
- 3. Encourage collaborative (Group) Learning in the class
- 4.Ask at least three HOTS (Higher order Thinking) questions in the class, which promotes critical thinking
- 5. Adopt Problem Based Learning (PBL), which fosters students' Analytical skills, develop thinking skills such as the ability to evaluate, generalize, and analyze information rather than simply recall it.
- 6. Show the different ways to solve the same problem and encourage the students to come up with their own creative ways to solve them.
- 7. Discuss how every concept can be applied to the real world and when that's possible, it helps improve the students' understanding.

MODULE-1

Transistor Biasing: Voltage Divider Bias, VDB Analysis, VDB Load line and Q point, Two supply Emitter Bias, Other types of Bias.

BJT AC models: Base Biased Amplifier, Emitter Biased Amplifier, Small Signal Operation, AC Beta, AC Resistance of the emitter diode, Two transistor models, Analyzing an amplifier, H parameters, Relations between R and H parameters.

Voltage Amplifiers: Voltage gain, Loading effect of Input Impedance.

CC Amplifiers: CC Amplifier, Output Impedance.

[Text1]

MODULE-2

MOSFET

Biasing in MOS amplifier circuits: Fixing VGS, Fixing VG, Drain to Gate feedback resistor.

Small signal operation and modelling: The DC bias point, signal current in drain, voltage gain, small signal equivalent circuit models, transconductance, The T equivalent circuit model.

MOSFET Amplifier configuration: Basic configurations, characterizing amplifiers, CS amplifier with and without source resistance, The Common Gate Amplifier, Source follower.

[Text 2]

MODULE-3

Linear Opamp Circuits: Summing Amplifier and D/A Converter, Nonlinear Op-amp Circuits: Comparator with zero reference, Comparator with non-zero references. Comparator with Hysteresis.

Oscillator: Theory of Sinusoidal Oscillation, The Wein-Bridge Oscillator, RC Phase Shift Oscillator, The Colpitts Oscillator, Hartley Oscillator, Crystal Oscillator.

The 555 timer: Monostable Operation, Astable Operation.

[Text1]

MODULE-4

Negative Feedback: Four Types of Negative Feedback, VCVS Voltage gain, Other VCVS Equations, ICVS Amplifier, VCIS Amplifier, ICIS Amplifier (No Mathematical Derivation).

Active Filters: Ideal Responses, First Order Stages, VCVS Unity Gain Second Order Low pass Filters, VCVS Equal Component Low Pass Filters, VCVS High Pass Filters, MFB Bandpass Filters, Bandstop Filters.

[Text1]

MODULE-5

Power Amplifiers: Amplifier terms, Two load lines, Class A Operation, Class B operation, Class B push pull emitter follower, Class C Operation.

Thyristors: The four layer Diode, SCR, SCR Phase control, Bidirectional Thyristors, IGBTs, Other Thyristors. [Text1]

PRACTICAL COMPONENT OF IPCC (Experiments can be conducted either using any circuit simulation

software or discrete components)

Sl.NO	Experiments			
1	Design and Test (i) Bridge Rectifier with Capacitor Input Filter (ii) Zener voltage regulator			
2	Design and Test Biased Clippers – a)Positive, b) Negative, c) Positive-Negative Positive and Negative Clampers with and without Reference.			
3	Plot the transfer and drain characteristics of a JFET and calculate its drain resistance, mutual conductance and amplification factor.			
4	Plot the transfer and drain characteristics of n-channel MOSFET and calculate its parameters, namely; drain resistance, mutual conductance and amplification factor.			
5	Design and test Emitter Follower			
6	Design and plot the frequency response of Common Source JFET/MOSFET amplifier			
7	Test the Opamp Comparator with zero and non zero reference and obtain the Hysteresis curve.			
8	Design and test Full wave Controlled rectifier using RC triggering circuit.			
9	Design and test Precision Half wave and full wave rectifiers using Opamp			
10	Design and test RC phase shift oscillator			

Course outcomes (Course Skill Set):

At the end of the course, the student will be able to:

- 1. Understand the characteristics of BJTs and FETs for switching and amplifier circuits.
- 2. Design and analyze amplifiers and oscillators with different circuit configurations and biasing conditions.
- 3. Understand the feedback topologies and approximations in the design of amplifiers and oscillators.
- 4. Design of circuits using linear ICs for wide range applications such as ADC, DAC, filters and timers.
- 5. Understand the power electronic device components and its functions for basic power electronic circuits.

Assessment Details (both CIE and SEE)

The weightage of Continuous Internal Evaluation (CIE) is 50% and for Semester End Exam (SEE) is 50%. The minimum passing mark for the CIE is 40% of the maximum marks (20 marks out of 50) and for the SEE minimum passing mark is 35% of the maximum marks (18 out of 50 marks). The student is declared as a pass in the course if he/she secures a minimum of 40% (40 marks out of 100) in the sum total of the CIE (Continuous Internal Evaluation) and SEE (Semester End Examination) taken together.

The IPCC means the practical portion integrated with the theory of the course. CIE marks for the theory component are **25 marks** and that for the practical component is **25 marks**.

CIE for the theory component of the IPCC

• 25 marks for the theory component are split into **15 marks** for two Internal Assessment Tests (Two Tests, each of 15 Marks with 01-hour duration, are to be conducted) and **10 marks** for other assessment methods mentioned in 220B4.2. The first test at the end of 40-50% coverage of the syllabus and the second test after covering 85-90% of the syllabus.

- Scaled-down marks of the sum of two tests and other assessment methods will be CIE marks for the theory component of IPCC (that is for **25 marks**).
- The student has to secure 40% of 25 marks to qualify in the CIE of the theory component of IPCC.

CIE for the practical component of the IPCC

- **15 marks** for the conduction of the experiment and preparation of laboratory record, and **10 marks** for the test to be conducted after the completion of all the laboratory sessions.
- On completion of every experiment/program in the laboratory, the students shall be evaluated including vivavoce and marks shall be awarded on the same day.
- The CIE marks awarded in the case of the Practical component shall be based on the continuous evaluation of
 the laboratory report. Each experiment report can be evaluated for 10 marks. Marks of all experiments' writeups are added and scaled down to 15 marks.
- The laboratory test **(duration 02/03 hours)** after completion of all the experiments shall be conducted for 50 marks and scaled down to **10 marks**.
- Scaled-down marks of write-up evaluations and tests added will be CIE marks for the laboratory component of IPCC for 25 marks.
- The student has to secure 40% of 25 marks to qualify in the CIE of the practical component of the IPCC.

SEE for IPCC

Theory SEE will be conducted by University as per the scheduled timetable, with common question papers for the course (duration 03 hours)

- 1. The question paper will have ten questions. Each question is set for 20 marks.
- 2. There will be 2 questions from each module. Each of the two questions under a module (with a maximum of 3 sub-questions), **should have a mix of topics** under that module.
- 3. The students have to answer 5 full questions, selecting one full question from each module.
- 4. Marks scored by the student shall be proportionally scaled down to 50 Marks

The theory portion of the IPCC shall be for both CIE and SEE, whereas the practical portion will have a CIE component only. Questions mentioned in the SEE paper may include questions from the practical component.

- The minimum marks to be secured in CIE to appear for SEE shall be 10 (40% of maximum marks-25) in the theory component and 10 (40% of maximum marks -25) in the practical component. The laboratory component of the IPCC shall be for CIE only. However, in SEE, the questions from the laboratory component shall be included. The maximum of 04/05 sub-questions are to be set from the practical component of IPCC, the total marks of all questions should not be more than 20 marks.
- SEE will be conducted for 100 marks and students shall secure 35% of the maximum marks to qualify for the SEE. Marks secured will be scaled down to 50.
- The student is declared as a pass in the course if he/she secures a minimum of 40% (40 marks out of 100) in the sum total of the CIE (Continuous Internal Evaluation) and SEE (Semester End Examination) taken together.

Suggested Learning Resources:

Books

- **1.** Albert Malvino, David J Bates, Electronic Principles, 7th Edition, Mc Graw Hill Education, 2017, ISBN:978-0-07-063424-4.
- 2. Microelectronic Circuits, Theory and Applications, Adel S Sedra, Kenneth C Smith, 6thEdition, Oxford, 2015.ISBN:978-0-19-808913-1

Web links and Video Lectures (e-Resources):

- 1. Integrated Electronics: Analog and Digital Circuits and Systems, Jacob Millman, Christos C. Halkias, McGraw-Hill, 2015.
- 2. Electronic Devices and Circuit, Boylestad & Nashelsky, Eleventh Edition, Pearson, January 2015.

Activity Based	Learning (Suggested	Activities in Class)/	' Practical Based learning